

Xiaoye Qin

List of Publications by Year in descending order

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33
papers

2,164
citations

430442

18
h-index

395343

33
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34
all docs

34
docs citations

34
times ranked

4157
citing authors

#	ARTICLE	IF	CITATIONS
1	Two-dimensional gallium nitride realized via graphene encapsulation. <i>Nature Materials</i> , 2016, 15, 1166-1171.	13.3	626
2	Covalent Nitrogen Doping and Compressive Strain in MoS ₂ by Remote N ₂ Plasma Exposure. <i>Nano Letters</i> , 2016, 16, 5437-5443.	4.5	323
3	MoS ₂ functionalization for ultra-thin atomic layer deposited dielectrics. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	171
4	Remote Plasma Oxidation and Atomic Layer Etching of MoS ₂ . <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 19119-19126.	4.0	145
5	Atomic Layer Deposition of a High- <i>k</i> Dielectric on MoS ₂ Using Trimethylaluminum and Ozone. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 11834-11838.	4.0	105
6	HfO ₂ on UV-O ₃ exposed transition metal dichalcogenides: interfacial reactions study. <i>2D Materials</i> , 2015, 2, 014004.	2.0	98
7	Realistic Metal-Graphene Contact Structures. <i>ACS Nano</i> , 2014, 8, 642-649.	7.3	93
8	Rapid Selective Etching of PMMA Residues from Transferred Graphene by Carbon Dioxide. <i>Journal of Physical Chemistry C</i> , 2013, 117, 23000-23008.	1.5	89
9	Al ₂ O ₃ on Black Phosphorus by Atomic Layer Deposition: An <i>in Situ</i> Interface Study. <i>ACS Applied Materials & Interfaces</i> , 2015, 7, 13038-13043.	4.0	81
10	A crystalline oxide passivation for Al ₂ O ₃ /AlGaIn/GaN. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	57
11	In situ atomic layer deposition half cycle study of Al ₂ O ₃ growth on AlGaIn. <i>Applied Physics Letters</i> , 2012, 101, 211604.	1.5	37
12	Schottky Barrier Height of Pd/MoS ₂ Contact by Large Area Photoemission Spectroscopy. <i>ACS Applied Materials & Interfaces</i> , 2017, 9, 38977-38983.	4.0	36
13	Effect of BaF ₂ Addition on Crystallization Kinetics and Dielectric Properties of B ₂ O ₃ -Nb ₂ O ₅ -SrO-BaO Glass-Ceramics. <i>Journal of the American Ceramic Society</i> , 2011, 94, 469-473.	1.9	33
14	Indium diffusion through high- <i>k</i> dielectrics in high- <i>k</i> /InP stacks. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	32
15	Impact of N ₂ and forming gas plasma exposure on the growth and interfacial characteristics of Al ₂ O ₃ on AlGaIn. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	29
16	A comparative study of atomic layer deposition of Al ₂ O ₃ and HfO ₂ on AlGaIn/GaN. <i>Journal of Materials Science: Materials in Electronics</i> , 2015, 26, 4638-4643.	1.1	25
17	<i>in situ</i> x-ray photoelectron spectroscopy and capacitance voltage characterization of plasma treatments for Al ₂ O ₃ /AlGaIn/GaN stacks. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	20
18	<i>in situ</i> plasma enhanced atomic layer deposition half cycle study of Al ₂ O ₃ on AlGaIn/GaN high electron mobility transistors. <i>Applied Physics Letters</i> , 2015, 107, .	1.5	18

#	ARTICLE	IF	CITATIONS
19	Surface and interfacial study of half cycle atomic layer deposited Al ₂ O ₃ on black phosphorus. <i>Microelectronic Engineering</i> , 2015, 147, 1-4.	1.1	15
20	In situ study of the role of substrate temperature during atomic layer deposition of HfO ₂ on InP. <i>Journal of Applied Physics</i> , 2013, 114, 154105.	1.1	14
21	<i>In situ</i> atomic layer deposition study of HfO ₂ growth on NH ₄ OH and atomic hydrogen treated Al _{0.25} Ga _{0.75} N. <i>Journal of Applied Physics</i> , 2013, 113, .	1.1	14
22	Silicon Interfacial Passivation Layer Chemistry for High- <i>k</i> /InP Interfaces. <i>ACS Applied Materials & Interfaces</i> , 2014, 6, 7340-7345.	4.0	14
23	<i>In situ</i> study of atomic layer deposition Al ₂ O ₃ on GaP (100). <i>Applied Physics Letters</i> , 2013, 103, 121604.	1.5	10
24	Formation of a ZnO/ZnS interface passivation layer on (NH ₄) ₂ S treated In _{0.53} Ga _{0.47} As: Electrical and in-situ X-ray photoelectron spectroscopy characterization. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 08PC02.	0.8	10
25	Dielectric and pyroelectric properties of Ba-modified lead lanthanum zirconate stannate titanate ceramics. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011, 176, 816-820.	1.7	9
26	<i>In situ</i> study of e-beam Al and Hf metal deposition on native oxide InP (100). <i>Journal of Applied Physics</i> , 2013, 114, .	1.1	9
27	In-situ XPS study of ALD ZnO passivation of p-In _{0.53} Ga _{0.47} As. <i>Electronic Materials Letters</i> , 2015, 11, 769-774.	1.0	9
28	A crystalline oxide passivation on In _{0.53} Ga _{0.47} As (100). <i>Journal of Applied Physics</i> , 2017, 121, .	1.1	9
29	Impact of Etch Processes on the Chemistry and Surface States of the Topological Insulator Bi ₂ Se ₃ . <i>ACS Applied Materials & Interfaces</i> , 2019, 11, 32144-32150.	4.0	9
30	<i>In situ</i> surface and interface study of crystalline (3Å–1)-O on InAs. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	8
31	Interface chemistry and surface morphology evolution study for InAs/Al ₂ O ₃ stacks upon in situ ultrahigh vacuum annealing. <i>Applied Surface Science</i> , 2018, 443, 567-574.	3.1	7
32	Digermene Deposition on Si(100) and Ge(100): from Adsorption Mechanism to Epitaxial Growth. <i>Journal of Physical Chemistry C</i> , 2014, 118, 482-493.	1.5	6
33	<i>In situ</i> isotope study of indium diffusion in InP/Al ₂ O ₃ stacks. <i>Applied Physics Letters</i> , 2022, 120, .	1.5	3